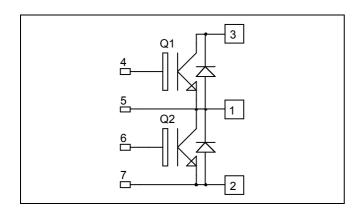


# Phase leg NPT IGBT Power Module

$$V_{CES} = 1200V$$
  
 $I_{C} = 300A$  @  $T_{C} = 80^{\circ}C$ 



#### Application

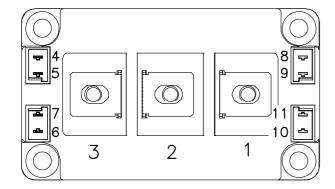
- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

#### **Features**

- Non Punch Through (NPT) FAST IGBT
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 50 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- High level of integration
- M6 power connectors

#### **Benefits**

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive  $T_C$  of  $V_{CEsat}$
- RoHS Compliant



#### **Absolute maximum ratings**

Symbol	Parameter		Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage		1200	V
$I_{\mathrm{C}}$	Continuous Collector Current	$T_C = 25^{\circ}C$	420	
	Continuous Conector Current	$T_C = 80$ °C	300	A
$I_{CM}$	Pulsed Collector Current	$T_C = 25^{\circ}C$	600	
$V_{GE}$	Gate – Emitter Voltage		±20	V
$P_D$	Maximum Power Dissipation	$T_C = 25$ °C	2100	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125$ °C	600A@1150V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



## All ratings @ $T_j = 25$ °C unless otherwise specified

### **Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				5	mA
V <sub>CE(on)</sub>	Collector Emitter on Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		3.2	3.7	V
		$I_C = 300A$ $T_j = 125$	$T_j = 125$ °C		3.9		·
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$ , $I_C = 12 \text{ mA}$		5.2	5.8	6.4	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

**Dynamic Characteristics** 

•	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V, V_{CE} = 25V$			19		nF
$C_{res}$	Reverse Transfer Capacitance	f = 1MHz		1.4		111	
$Q_{G}$	Gate charge	V <sub>GE</sub> =±15V, I <sub>C</sub> =300A V <sub>CE</sub> =600V			3		μС
$T_{d(on)}$	Turn-on Delay Time	Inductive Switchi	ing (25°C)		100		
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15V$			60		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$ $I_{C} = 300A$		530		ns	
$T_{\mathrm{f}}$	Fall Time	$R_G = 3.3\Omega$		30			
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_{C} = 300A$ $R_{G} = 3.3\Omega$			110		ns
$T_{r}$	Rise Time				70		
$T_{d(off)}$	Turn-off Delay Time				550		
$T_{\rm f}$	Fall Time				40		
Eon	Turn On Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$	$T_j = 125$ °C		25		mJ
$E_{\text{off}}$	Turn Off Energy	$I_C = 300A$ $R_G = 3.3\Omega$	$T_j = 125$ °C		21		1113
$I_{sc}$	Short Circuit data	$V_{GE} \le 15V$ ; $V_{Bus} = 900V$ $t_p \le 10\mu s$ ; $T_j = 125^{\circ}C$			2000		A

### Reverse diode ratings and characteristics

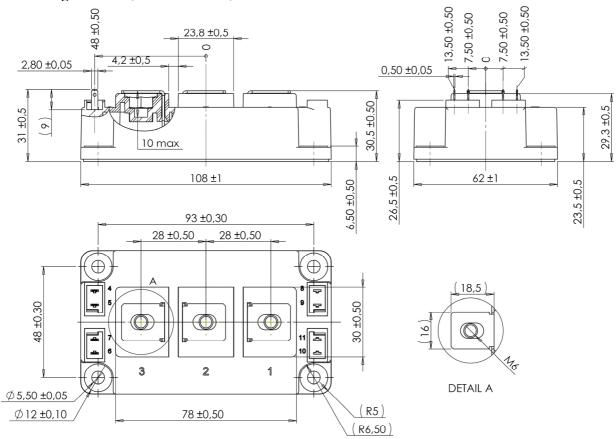
Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage			1200			V
T	Maximum Reverse Leakage Current	V <sub>R</sub> =1200V	$T_j = 25^{\circ}C$			750	4
$I_{RRM}$			$T_j = 125$ °C			1000	μΑ
$I_F$	DC Forward Current		Tc = 80°C		300		A
$V_{\mathrm{F}}$	Diode Forward Voltage	$I_F = 300A$	$T_i = 25$ °C		2.1		V
V F			$T_i = 125$ °C		1.9		
t <sub>rr</sub>	Reverse Recovery Time	$I_F = 300A$ $V_R = 600V$ $di/dt = 4500A/\mu s$	$T_j = 25^{\circ}C$		120		ns
			$T_j = 125$ °C		210		115
Q <sub>rr</sub>	Reverse Recovery Charge		$T_j = 25$ °C		19		uС
			$T_{j} = 125^{\circ}C$		53		μС
E <sub>rr</sub> Reverse Recovery Energy	Payarsa Pagayary Engray		$T_j = 25$ °C		7		mJ
		$T_j = 125$ °C		15		1111	



## Thermal and package characteristics

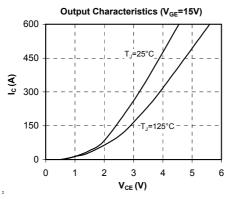
Symbol	Characteristic			Min	Тур	Max	Unit
D	Junction to Case Thermal Resistance  IGBT  Diode				0.06	°C/W	
$R_{thJC}$					0.12		
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
$T_{J}$	Operating junction temperature range		-40		150		
$T_{STG}$	Storage Temperature Range			-40		125	°C
$T_{\rm C}$	Operating Case Temperature			-40		125	
Torque	Mounting torque For terminals  To Heatsink	For terminals	M6	3		5	N.m
		To Heatsink	M6	3		5	19.111
Wt	Package Weight					350	g

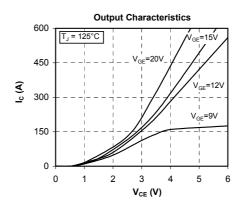
### D3 Package outline (dimensions in mm)

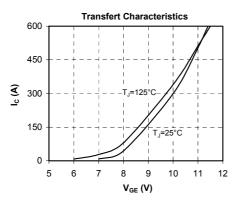


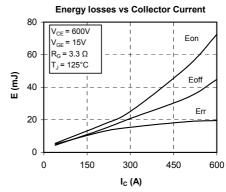


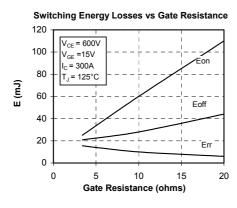
### **Typical Performance Curve**

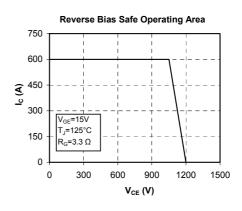


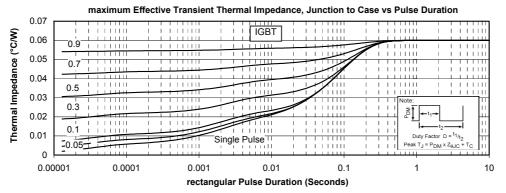




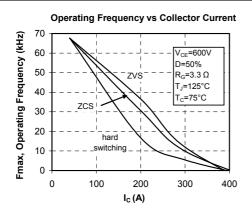


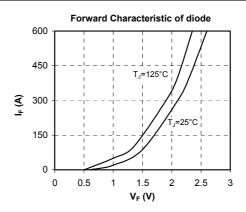


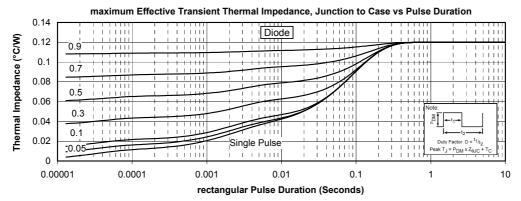














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